

In the Claims:

1. (Previously Presented) A transistor device comprising:
 - a semiconductor region having a top surface;
 - a source region in the semiconductor region;
 - a drain region in the semiconductor region;
 - a channel region in the semiconductor region between the source region and the drain region;
 - an impurity region within the channel region and spaced from the top surface, the impurity region having a first outer boundary that is proximate, but laterally spaced apart from the source region and a second outer boundary proximate, but laterally spaced apart from the drain region;
 - a gate overlying the channel region; and
 - a gate dielectric between the gate and the channel region.
2. (Original) The device of claim 1 wherein the semiconductor region comprises a region of monocrystalline silicon.
3. (Original) The device of claim 2 wherein the semiconductor region comprises a silicon substrate.
4. (Original) The device of claim 1 wherein the source and drain regions extend into the semiconductor region a first distance, and wherein the impurity region is spaced from the top surface by a distance less than the first distance.
5. (Original) The device of claim 1 wherein the gate dielectric comprises silicon dioxide.

6. (Original) The device of claim 1 wherein the impurity region comprises a region of an implanted oxygen bearing species in the channel region.
7. (Original) The device of claim 1 wherein the channel region comprises a strained channel region.
8. (Original) The device of claim 1 and further comprising:
a first sidewall spacer adjacent a first sidewall of the gate;
a second sidewall spacer adjacent a second sidewall of the gate;
a lightly doped drain region within the semiconductor region adjacent the drain region,
the lightly doped drain region disposed beneath the first sidewall; and
a lightly doped source region within the semiconductor region adjacent the source region,
the lightly doped source region disposed beneath the second sidewall.
9. (Original) The device of claim 1 and further comprising a second transistor, the second transistor including:
a second source region in the semiconductor region;
a second drain region in the semiconductor region;
a second channel region in the semiconductor region between the second source region
and the second drain region;
a second gate overlying the channel region; and
a second gate dielectric between the gate and the channel region.
10. (Previously Presented) The device of claim 9 further comprising a second impurity region within the second channel region and spaced from the top surface, the second impurity

region having a first outer boundary proximate, but laterally spaced apart from the source region and a second outer boundary that is proximate, but laterally spaced apart from the drain region.

11. (Original) The device of claim 9 wherein the second transistor does not include an impurity region within the second channel region.

12. (Original) The device of claim 9 wherein the second transistor device comprises an n-channel transistor.